

ABSTRACT OF THE DISCLOSURE

The invention includes a method of forming a transistor gate. One or more conductive materials are formed over a semiconductor substrate, and a block is formed over the one or more conductive materials. The block comprises a photoresist mass and a material other than photoresist which is against the photoresist. A pattern is transferred from the block to the one or more conductive materials to pattern a transistor gate construction from the one or more conductive materials.